TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC5713

High-Speed Switching Applications DC-DC Converter Applications Strobe Applications

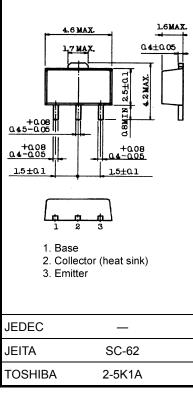
- High DC current gain: $h_{FE} = 400$ to 1000 (IC = 0.5 A)
- Low collector-emitter saturation voltage: $V_{CE (sat)} = 0.15 \text{ V (max)}$
- High-speed switching: $t_f = 50 \text{ ns (typ.)}$

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit | |
|-----------------------------|----------|------------------|------------|------|--|
| Collector-base voltage | | V _{CBO} | 20 | V | |
| Collector-emitter voltage | | V _{CEX} | 15 | V | |
| Collector-emitter voltage | | V _{CEO} | 10 | V | |
| Emitter-base voltage | | V _{EBO} | 7 | V | |
| Collector current | DC | Ic | 4 | А | |
| | Pulse | I _{CP} | 7 | | |
| Base current | | ΙΒ | 400 | mA | |
| Collector power dissipation | DC | PC | 1.0 | W | |
| | t = 10 s | (Note 1) | 2.5 | | |
| Junction temperature | | Tj | 150 | °C | |
| Storage temperature range | | T _{stg} | -55 to 150 | °C | |

Industrial Applications

Unit: mm



Weight: 0.05 g (typ.)

- Note 1: Mounted on an FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)
- Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Energy istics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------------|--------------|-----------------------|---|-----|------|------|------|
| Collector cut-off current | | I _{CBO} | $V_{CB} = 20 \text{ V}, I_{E} = 0$ | _ | _ | 100 | nA |
| Emitter cut-off current | | I _{EBO} | V _{EB} = 7 V, I _C = 0 | _ | _ | 100 | nA |
| Collector-emitter breakdown voltage | | V (BR) CEO | $I_C = 10 \text{ mA}, I_B = 0$ | 10 | _ | _ | V |
| DC current gain | | h _{FE} (1) | V _{CE} = 2 V, I _C = 0.5 A | 400 | _ | 1000 | |
| | | h _{FE} (2) | V _{CE} = 2 V, I _C = 1.6 A | 200 | _ | _ | |
| Collector-emitter saturation voltage | | V _{CE} (sat) | I _C = 1.6 A, I _B = 32 mA | _ | _ | 0.15 | V |
| Base-emitter saturation voltage | | V _{BE} (sat) | I _C = 1.6 A, I _B = 32 mA | _ | _ | 1.10 | V |
| Collector output capacitance | | C _{ob} | V _{CB} = 10 V, I _E = 0, f = 1 MHz | _ | 28 | _ | pF |
| Switching time | Rise time | t _r | See Figure 1 circuit diagram. | _ | 110 | _ | ns |
| | Storage time | t _{stg} | $V_{CC} \simeq 6 \text{ V}, R_L = 3.75 \Omega$ | _ | 150 | _ | |
| | Fall time | t _f | $I_{B1} = -I_{B2} = 53 \text{ mA}$ | _ | 50 | _ | |

Marking

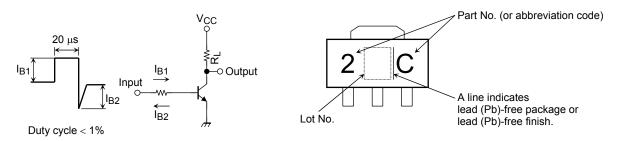
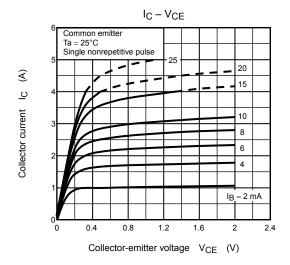
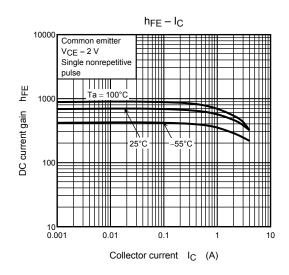
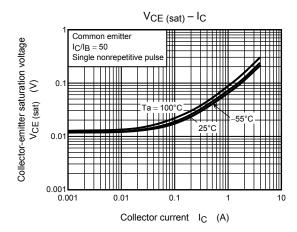
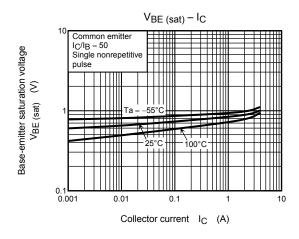


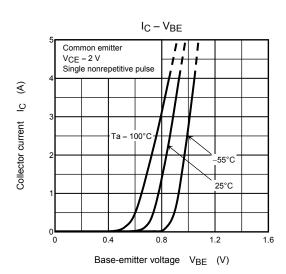
Figure 1 Switching Time Test Circuit & Timing Chart

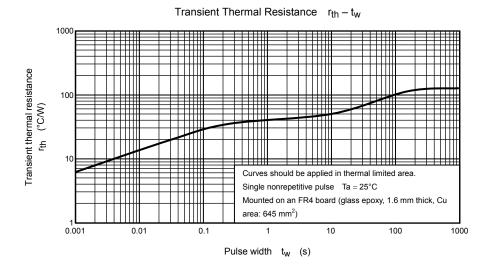


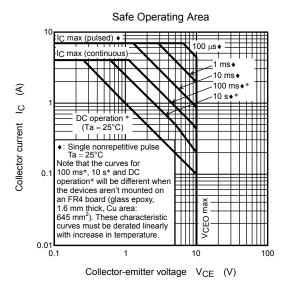












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